

**WHAT IS CLAIMED IS:**

1. Apparatus, comprising:
  - a) first and second mounds of dielectric, respectively encapsulating first and second conductors;
  - b) a third dielectric, filling a valley between the first and second mounds of dielectric, and encapsulating a third conductor; and
  - c) a first ground shield deposited on at least sides of the first and second mounds of dielectric, abutting the third dielectric.
2. The apparatus of claim 1, further comprising a second ground shield on which the first and second mounds of dielectric are deposited; wherein the first ground shield extends to the second ground shield.
3. The apparatus of claim 2, further comprising a third ground shield deposited on the third dielectric; the third ground shield contacting the first ground shield.
4. The apparatus of claim 1, wherein the dielectrics are glass dielectrics.
5. The apparatus of claim 1, wherein the dielectrics are KQ dielectrics.
6. The apparatus of claim 5, wherein the KQ dielectrics are KQ CL-90-7858 dielectrics.

7. The apparatus of claim 1, wherein the dielectrics are thickfilm dielectrics.
8. A method for forming shielded transmission lines, comprising:
  - a) depositing first and second lower mounds of dielectric on a first ground shield;
  - b) depositing conductors on the first and second lower mounds of dielectric;
  - c) depositing first and second upper mounds of dielectric on the first and second lower mounds of dielectric;
  - d) depositing a second ground shield over the first and second dielectrics;
  - e) depositing a third lower dielectric in a valley between the first and second dielectrics;
  - f) depositing a conductor on the third lower dielectric;
  - g) depositing a third upper dielectric on the third lower dielectric; and
  - h) depositing a third ground shield over the third upper dielectric.
9. The method of claim 8, wherein the dielectrics are glass dielectrics.
10. The method of claim 8, wherein the dielectrics are KQ dielectrics.
11. The method of claim 10, wherein the KQ dielectrics are KQ CL-90-7858 dielectrics.

12. The method of claim 8, wherein the dielectrics are thickfilm dielectrics.

13. A method for forming shielded transmission lines, comprising:

- a) depositing first and second lower mounds of dielectric on a first ground shield;
- b) depositing ground shield walls on sides of the first and second lower mounds of dielectric;
- c) depositing a third lower dielectric in a valley between the first and second lower mounds of dielectric;
- d) depositing conductors on each of the lower mounds of dielectric;
- e) depositing first and second upper mounds of dielectric on the first and second lower mounds of dielectric;
- f) depositing ground shield caps over the first and second upper mounds of dielectric;
- g) depositing a third upper dielectric on the third lower dielectric; and
- h) depositing a second ground shield over the third upper dielectric.

14. The method of claim 13, wherein the dielectrics are glass dielectrics.

15. The method of claim 13, wherein the dielectrics are KQ dielectrics.

16. The method of claim 15, wherein the KQ dielectrics are KQ CL-90-7858 dielectrics.

17. The method of claim 13, further comprising polishing the lower dielectrics prior to depositing the conductors.
18. The method of claim 13, wherein each of the dielectrics is deposited by printing multiple layers of thickfilm dielectric and then firing the layers.
19. The method of claim 18, further comprising polishing the lower dielectrics prior to depositing the conductors.
20. The method of claim 13, wherein the height of the third lower dielectric is less than the heights of the first and second lower mounds of dielectric.